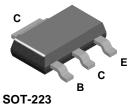
BCP52



BCP52



PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switching circuits requiring collector currents to 1.0 A. Sourced from Process 78.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.2	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		BCP52		
P _D	Total Device Dissipation	1.5	W	
	Derate above 25°C	12	mW/°C	
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	83.3	°C/W	

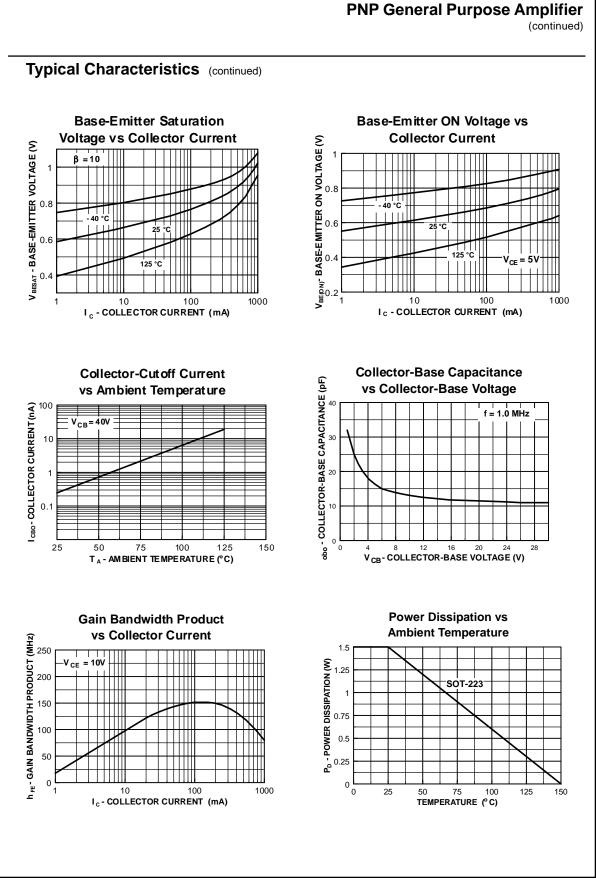
PNP General Purpose Amplifier (continued)

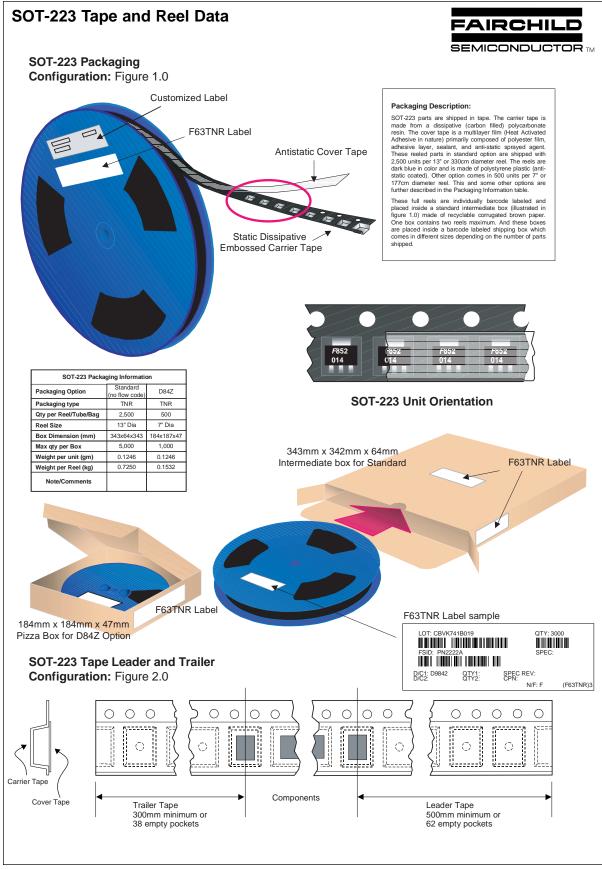
ed)

$V_{(BR)CBO} = Collector-Base Breakdown Voltage} = I_{C} = 100 \ \mu\text{A}, I_{E} = 0 = 60$ $V_{(BR)EBO} = Emitter-Base Breakdown Voltage} = I_{E} = 10 \ \mu\text{A}, I_{C} = 0$ $Collector-Cutoff Current = V_{CB} = 30 \ V, I_{E} = 0, T_{A} = 125^{\circ}\text{C} = 100 \ V_{CB} = 30 \ V, I_{E} = 0, T_{A} = 125^{\circ}\text{C} = 100 \ V_{CB} = 30 \ V, I_{E} = 0, T_{A} = 125^{\circ}\text{C} = 100 \ V_{CB} = 30 \ V, I_{E} = 0, T_{A} = 125^{\circ}\text{C} = 100 \ V_{CB} = 30 \ V, I_{E} = 0, T_{A} = 125^{\circ}\text{C} = 100 \ V_{CB} = 30 \ V, I_{E} = 0, T_{A} = 125^{\circ}\text{C} = 100 \ V_{CB} = 30 \ V, I_{E} = 0, T_{A} = 125^{\circ}\text{C} = 100 \ V_{CB} = 500 \ V_{CB} = 5.0 \ V, I_{C} = 0$ $ON CHARACTERISTICS$ $n_{FE} = DC Current Gain I_{C} = 5.0 \ mA, V_{CE} = 2.0 \ V = 25 \ V_{C} = 150 \ mA, V_{CE} = 2.0 \ V = 25 \ V_{CE} = 2.0 \ V = 25 \ V_{CE} = 2.0 \ V = 25 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 1.0 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 1.0 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 1.0 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 1.0 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 1.0 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 1.0 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 1.0 \ V_{CE} = 2.0 \ V = 1.0 \ V_{CE} = 1.0 \ V_{C$		Parameter	Test Conditions	Min	Max	Units
$V_{(BR)CBO} \qquad Collector-Base Breakdown Voltage V_{(BR)CBO} Collector-Cutoff Current V_{(BR)EBO} Collector-Cutoff Current V_{CB} = 30 V, I_E = 0 10 V_{CB} = 5.0 V, I_C = 0 10 ON CHARACTERISTICS V_{CE} = 2.0 V I_C = 150 mA, V_{CE} = 2.0 V I_C = 500 mA, V_{CE} = 2.0 V I_O NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors. Typical Pulsed Current Gain vs Collector Current vs Collector Current Voltage vs Collector Current V V V V V V V V V V V V V V V V V V $	OFF CHA	RACTERISTICS				
Vigneted VignetedEmitter-Base Breakdown VoltageIE = 10 µA, Ic = 05.0Vigneted (csoCollector-Cutoff CurrentVcB = 30 V, IE = 0 VcB = 30 V, IE = 0, TA = 125°C100 100Vigneted VeB = 5.0 V, Ic = 0Emitter-Cutoff CurrentVcB = 5.0 V, Ic = 0100ON CHARACTERISTICSON CHARACTERISTICSNFEDC Current GainIc = 5.0 mA, VcE = 2.0 V Ic = 150 mA, VcE = 2.0 V Ic = 500 mA, VcE = 2.0 V Ic = 500 mA, VcE = 2.0 V250 Ic = 500 mA, VcE = 2.0 V Ic = 150 mAVoE(sat)Collector-Emitter Saturation Voltage Ic = 500 mA, VcE = 2.0 V1.0NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.Collector-Emitter Saturation Voltage vs Collector Current Voltage vs Collector Current	V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	60		V
$I_{CBO} \qquad Collector-Cutoff Current \qquad V_{CB} = 30 V, I_E = 0 \\ V_{CB} = 30 V, I_E = 0, T_A = 125^{\circ}C \qquad 10 \\ I_{CBO} \qquad Emitter-Cutoff Current \qquad V_{EB} = 5.0 V, I_C = 0 \qquad 10 \\ \hline NOR CHARACTERISTICS \\ DC Current Gain \qquad I_C = 5.0 mA, V_{CE} = 2.0 V & 25 \\ I_C = 150 mA, V_{CE} = 2.0 V & 25 \\ I_C = 500 mA, V_{CE} = 2.0 V & 25 \\ I_C = 500 mA, V_{CE} = 2.0 V & 25 \\ V_{CE(sat)} \qquad Collector-Emitter Saturation Voltage \qquad I_C = 500 mA, V_{CE} = 2.0 V & 1.0 \\ \hline NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors. \\ \hline Typical Pulsed Current Gain \\ vs Collector Current $	V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	60		V
$V_{CE} = 30 V, I_E = 0, T_A = 125^{\circ}C$ 10 I_{EBO} Emitter-Cutoff Current V_{EB} = 5.0 V, I_C = 0 10 ON CHARACTERISTICS h_{FE} $DC Current Gain$ $I_C = 5.0 mA, V_{CE} = 2.0 V$ 25 $I_C = 150 mA, V_{CE} = 2.0 V$ 25 $V_{CE(Bal)}$ Collector-Emitter Saturation Voltage $I_C = 500 mA, V_{CE} = 2.0 V$ 25 $V_{CE(Bal)}$ Collector-Emitter On Voltage $I_C = 500 mA, V_{CE} = 2.0 V$ 1.0 NoTE: All voltages (V) and currents (A) are negative polarity for PNP transistors. $Typical Pulsed Current Gain$ $vs Collector Current \int_{0.6}^{0.6} \int_{0.5}^{0.6} \int_{0.6}^{0.6} \int_{0.5}^{0.6} \int_{0.6}^{0.6} \int_{$	V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	5.0		V
ON CHARACTERISTICS $T_{FE} \qquad DC Current Gain \qquad l_{C} = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 25 \\ l_{C} = 150 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 25 \\ l_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 25 \\ l_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 25 \\ V_{CE(sat)} \qquad Collector-Emitter Saturation Voltage \qquad l_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \\ \hline V_{BE(on)} \qquad Base-Emitter On Voltage \qquad l_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \\ \hline NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors. \\ \hline Typical Characteristics \\ \hline V_{0E} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \\ \hline V_{0E} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \\ \hline OTE: All voltages (V) and currents (A) are negative polarity for PNP transistors. \\ \hline Collector-Emitter Saturation vs Collector Current Gain vs Collector Curren$	СВО	Collector-Cutoff Current				nA
$\begin{tabular}{l l l l l l l l l l l l l l l l l l l $	EBO	Emitter-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0, I_A = 125^{\circ}\text{C}$ $V_{EB} = 5.0 \text{ V}, I_C = 0$			μΑ μΑ
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	ON CHAR	ACTERISTICS				
$I_{C} = 150 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 40 \qquad 250 \qquad I_{C} = 500 \text{ mA}, V_{OE} = 2.0 \text{ V} \qquad 25 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{OE} = 2.0 \text{ V} \qquad 25 \qquad 0.5 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, I_{B} = 50 \text{ mA} \qquad 0.5 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad 0.5 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad 1.0 \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V} \qquad I_{C} = 500 \text{ mA}, V_{CE} = 500 \text{ mA},$			$I_{c} = 5.0 \text{ mA}$, $V_{c_{c}} = 2.0 \text{ V}$	25		
V _{CE(sat)} Collector-Emitter Saturation Voltage I _c = 500 mA, I _B = 50 mA 0.5 V _{BE(on)} Base-Emitter On Voltage I _c = 500 mA, V _{CE} = 2.0 V 1.0 NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors. Collector-Emitter Saturation Voltage 0.5 Typical Characteristics Collector-Emitter Saturation vs Collector Current Output to the saturation vs Collector Current Collector Current 400	-1 E		$I_{C} = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}$	40	250	
Typical Pulsed Current Gain Collector Current Variation Second Vision Collector Current Variation Second Vision Collector Current Vision Second V	,			25	0.5	
NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors. Typical Characteristics Typical Pulsed Current Gain vs Collector Current $V_{0tage} vs Collector Current$ $V_{0tage} vs Collector Current$ $V_{0tage} vs Collector Current$ $V_{0tage} vs Collector Current$ $V_{0tage} vs Collector Current$		-				V
Typical Characteristics Typical Pulsed Current Gain vs Collector Current $400^{-0.6}_{-0.5}$ $300^{-0.6}_{-0.5}$ $200^{-0.6}_{-0.5}$	/ _{BE(on)}	Base-Emitter On Voltage	$I_{\rm C} = 500$ mA, $V_{\rm CE} = 2.0$ V		1.0	V
Name V _{CE} = 5V Image: Constraint of the second se		vs Collector Current	$\widehat{E} \qquad \text{Voltage vs} ($	Collector		
NO 125 °C 125 °C V 100 -40 °C	R N		9 0.5			·40 °C /
200 25 °C 100 -40 °C 100 -40 °C 100 -40 °C 100 -40 °C 100 -40 °C 100 -40 °C 100 -40 °C 100 -40 °C			й 0.4		25 °C	
S120 25 °C 0.3 V310 -40 °C 0.1	300 H					
Image: Constraint of the second se		125 °C	N			
	000 URI 200 UR	125 °C	NO - 201			411
		25 °C	₩ 0.3 80 5 0.2			
	200 100 100 100 100 100 100 100 100 100	25 °C			1	25 °C —
$ \begin{array}{c} $	200 001 001 001 001 001 001 001 001 001	25 °C	9.3 80.2 9.0.2 9.1 0.1		12	25 °C —
I_c - COLLECTOR CURRENT (A) \rightarrow I_c - COLLECTOR CURRENT (A)	10000 000 000 000 000 000 000 000 000 0	-40 °C		0.1		25°C 1 1.5
	H ^{EE} - TYPICAL PULSED CURI	-40 °C		0.1 ECTOR CUR		25 °C —
	h Fe- TYPICAL PULSED CURI	-40 °C		0.1 ECTOR CUR		25 °C —
	h _{FE} -TYPICAL PULSED CURI 001 007 001 001 001 001	-40 °C		0.1 ECTOR CUR		25 °C —
	h FE- TYPICAL PULSED CURI 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	-40 °C		0.1 ECTOR CUR		25 °C —
	P ¹ P ¹ P ¹ P ¹ P ¹ P ¹ P ¹ P ¹	-40 °C		0.1 ECTOR CUR		25 °C —
	Pier- TYPICAL PULSED CURI 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	-40 °C	۳ 0.3 ۳ 0.3 0.2 0.1 1 0.1 1 0.1	0.1 ECTOR CUR		25 °C —
	h Fe-TYPICAL PULSED CURI	-40 °C	1 NH 0.3 ND 0.2 H 0.3 0.2 0.01 1 C - COLL	0.1 ECTOR CUR		25 °C —
	h FE- TYPICAL PULSED CURI 0 0 0 00 00 0.0	-40 °C	1 1 1 1 1 1 1 1 1 1 1 1 1 1	0.1 ECTOR CUF		25 °C —

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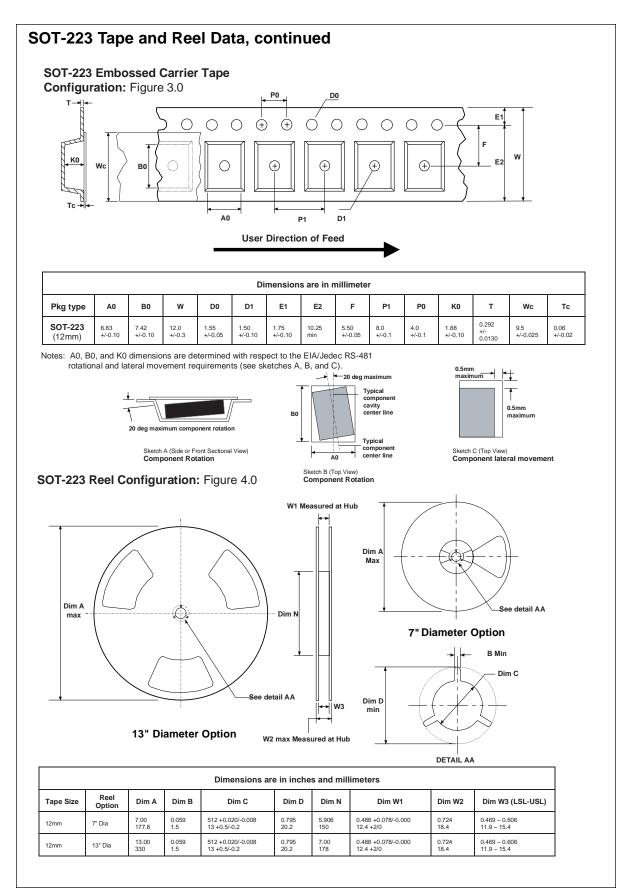
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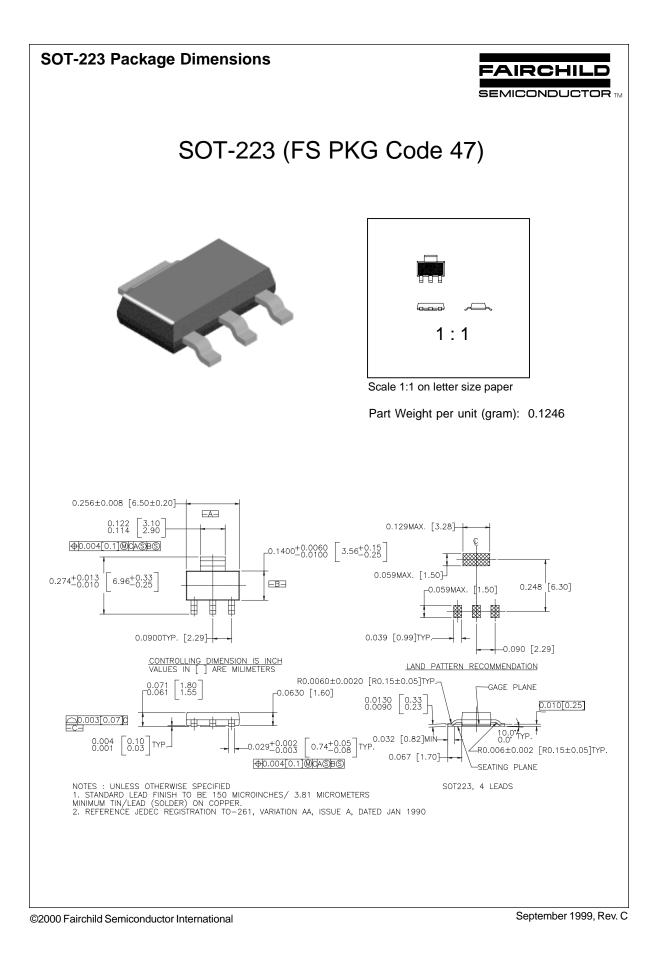


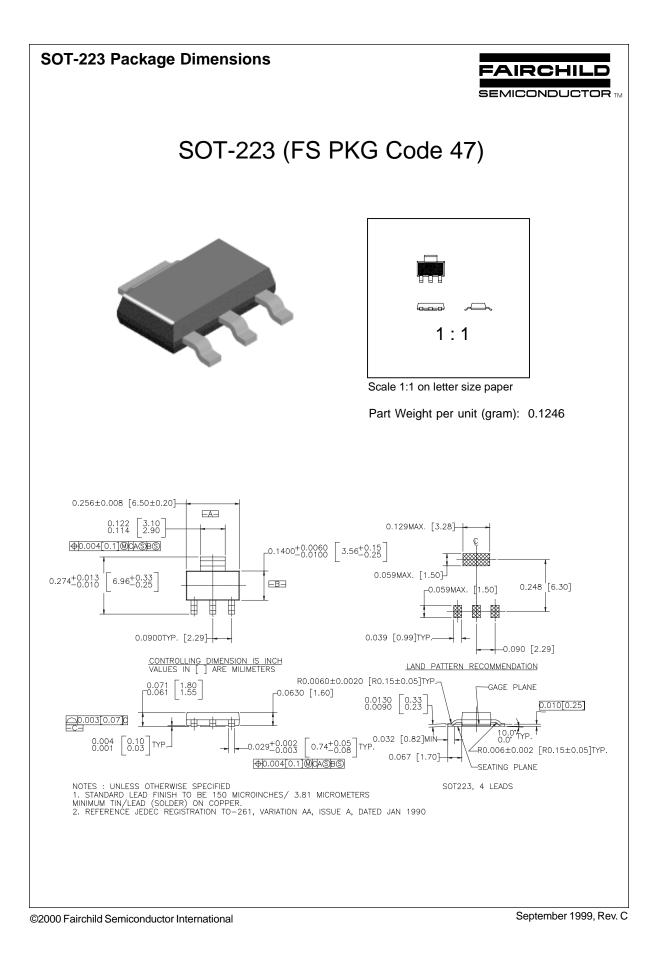


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	1	Rev G